



N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY						
V _{DS} (V)	$r_{DS(on)}(\Omega)$	I _D (A)				
30	0.0120 @ V _{GS} = 10 V	11				
	0.0175 @ V _{GS} = 4.5 V	9.5				

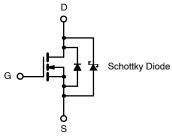
SCHOTTKY PRODUCT SUMMARY					
V _{DS} (V)	V _{SD} (v) Diode Forward Voltage	I _F (A)			
30	0.53 V @ 3 A	4			

SO-8 8 D D Top View

Ordering Information: Si4852DY Si4852DY-T1 (with Tape and Reel)

FEATURES

- LITTLE FOOT® Plus
- 100% R_g Tested



ABSOLUTE MAXIMUM RA		1 1		_	
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage (MOSFET)		V _{DS}	30		V
Reverse Voltage (Schottky)		V _{DA}	30		
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current (T, = 150°C)	T _A = 25°C		11	8.7	
(MOSFET) ^a	T _A = 70°C	l _D	9.0	7.0	
Pulsed Drain Current (MOSFET)		I _{DM}	50		╗,
Continuous Source Current (MOSFET Diode Conduction) ^a		I _S	2.3	1.3	_ A
Average Foward Current (Schottky)		I _F	4.0	2.5	
Pulsed Foward Current (Schottky)		I _{FM}	50		7
Mariana Para Pirai Aira (MOCET)	T _A = 25°C		2.5	1.47	
Maximum Power Dissipation (MOSFET) ^a	T _A = 70°C	1 , —	1.6	0.94	w
Maximum Power Dissipation (Schottky) ^a	T _A = 25°C	P _D	2.27	1.38	vv
	T _A = 70°C		1.45	0.88	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS								
			MOSFET		Schottky			
Parameter		Symbol	Тур	Max	Тур	Max	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	_	40	50	45	55		
	Steady-State	R _{thJA}	72	85	75	90	°C/W	
Maximum Junction-to-Foot (Drain)	Steady-State	R _{thJF}	18	22	20	25		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

Si4852DY

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MOSFET SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED).							
Parameter	Symbol	Test Condition		Тура	Max	Unit	
Static			- 1	•	•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			±100	nA	
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$		0.007	0.100	mA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \ V, V_{GS} = 0 \ V, T_{J} = 100 ^{\circ} C$		1.5	10		
		$V_{DS} = 24 \text{ V, } V_{GS} = 0 \text{ V, } T_{J} = 125^{\circ}\text{C}$	6.5 20			7	
On-State Drain Current ^b	I _{D(on)}	$V_{DS \ge 5} V$, $V_{GS} = 10 V$	20			Α	
Drain-Source On-State Resistance ^b		$V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$		0.0100	0.0120		
	r _{DS(on)}	$V_{GS} = 4.5 \ V, I_D = 9.5 A$		0.0145	0.0175	Ω	
Forward Transconductance ^b	9fs	$V_{DS} = 15 \text{ V}, I_D = 11 \text{ A}$		28		S	
Schottky Diode Forward Voltage ^b	.,	$I_S = 3.0 \text{ A}, V_{GS} = 0 \text{ V}$		0.485	0.53	,,	
	V _{SD}	$I_S = 3.0 \text{ A}, V_{GS} = 0 \text{ V}, T_J = 125^{\circ}\text{C}$	0.416 0.		0.47	_ v	
Dynamic ^a	<u>.</u>						
Total Gate Charge	Qg			24	35		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, \ V_{GS} = 5 \text{ V}, \ I_D = 11 \text{ A}$		9		nC	
Gate-Drain Charge	Q _{gd}			7.5		1	
Gate Resistance	R _g		0.5		2.6	Ω	
Turn-On Delay Time	t _{d(on)}			17	30		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{I} = 15 \Omega$		10	20	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 6 \Omega$		60	100		
Fall Time	t _f			18	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3.ο A, di/dt = 100 A/μs		40	70		

SCHOTTKY SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit	
Forward Voltage Drop	.,	I _F = 3.0 A	0.485 0.53		.,		
	V _F	I _F = 3.0 A, T _J = 125°C		0.416	0.47	٧	
Maximum Reverse Leakage Current		V _r = 24 V		0.007	0.100		
	I _{rm}	V _r = 24 V, T _J = 100°C		1.5	10	mA	
		V _r = -24 V, T _J = 125°C		6.4	20		
Junction Capacitance	C _T	V _r = 10 V		115		pF	

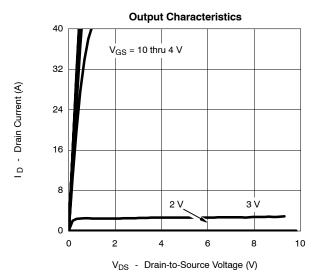
Notes a. Guaranteed by design, not subject to production testing. b. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$.

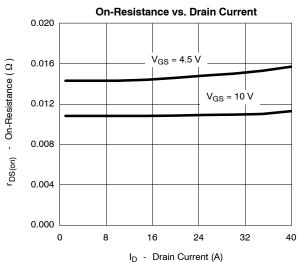


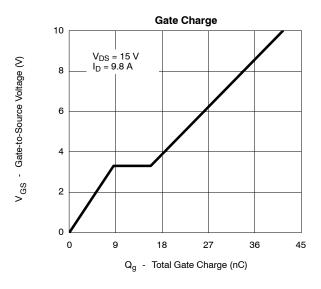


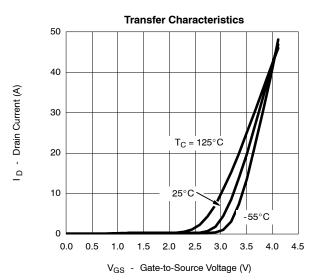
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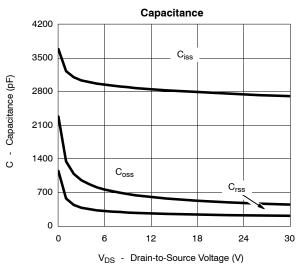
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

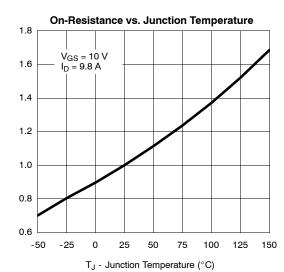










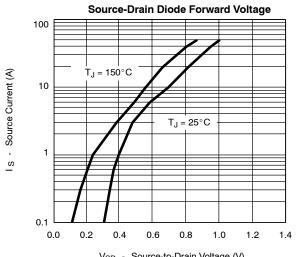


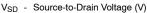
^rDS(on) - On-Resistance (Ω) (Normalized)

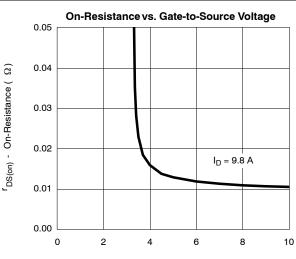
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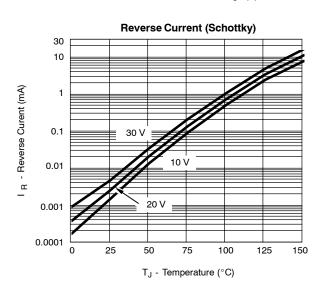
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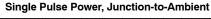


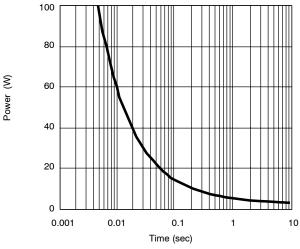




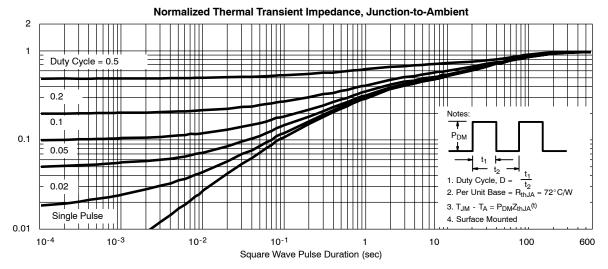
V_{GS} - Gate-to-Source Voltage (V)









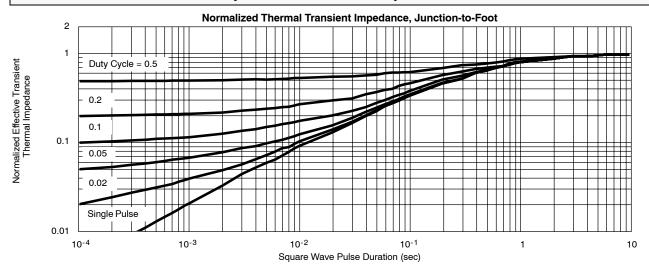






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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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